

# Schottky barrier diode

## RB531XN

### ●Applications

Rectifying small power

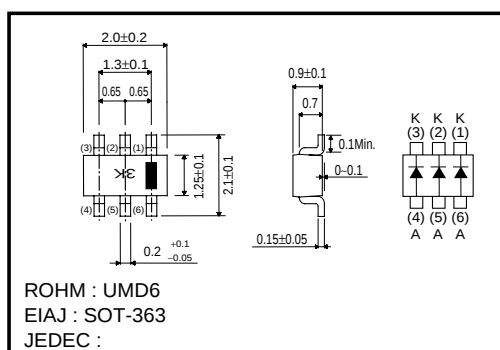
### ●Features

- 1) Small mold type. (UMD6)
- 2) High reliability.

### ●Construction

Silicon epitaxial planar

### ●External dimensions (Unit : mm)



### ●Absolute maximum ratings (Ta=25°C)

| Parameter                     | Symbol    | Limits      | Unit |
|-------------------------------|-----------|-------------|------|
| DC reverse voltage            | $V_R$     | 30          | V    |
| Mean rectifying current *1    | $I_O$     | 100         | mA   |
| Peak forward surge current *2 | $I_{FSM}$ | 1           | A    |
| Junction temperature          | $T_j$     | 125         | °C   |
| Storage temperature           | $T_{stg}$ | -40 to +125 | °C   |

\*1 Rating of per diode.

\*2 60Hz for 1  $\varnothing$

### ●Electrical characteristics (Ta=25°C)

| Parameter       | Symbol   | Min. | Typ. | Max.  | Unit          | Conditions         |
|-----------------|----------|------|------|-------|---------------|--------------------|
| Forward voltage | $V_{F1}$ | —    | —    | 0.300 | V             | $I_F=10\text{mA}$  |
|                 | $V_{F2}$ | —    | —    | 0.430 | V             | $I_F=100\text{mA}$ |
| Reverse current | $I_R$    | —    | —    | 20    | $\mu\text{A}$ | $V_R=10\text{V}$   |

Note) Please pay attention to static electricity when handling.

## Diodes

## ●Electrical characteristic curves (Ta=25°C)

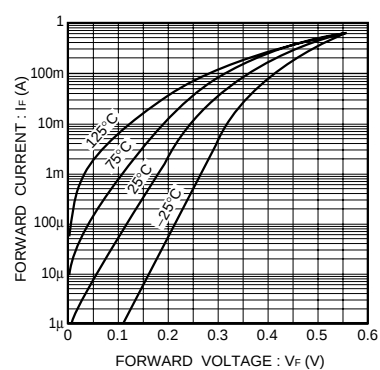


Fig.1 Forward characteristics

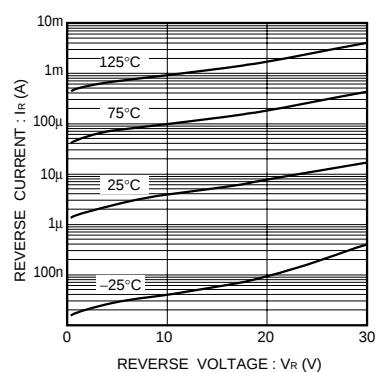


Fig.2 Reverse characteristics

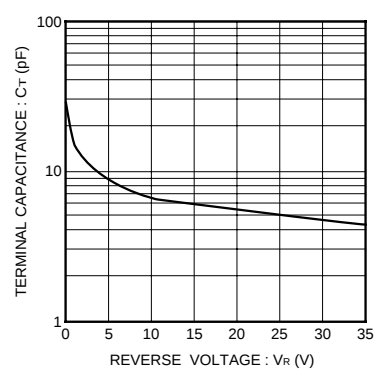


Fig.3 Capacitance between terminals characteristics